

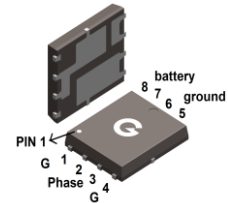
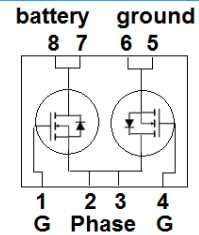
Features

- Half-Bridge
- N-channel Enhancement mode
- Normal Level
- RoHS compliant with Halogen-free
- Qualified to AEC-Q101 Standards

HF

Mechanical Data

- Case: DFN5X6HB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



DFN5X6HB

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBL04N070H	DFN5X6HB	5000 pcs / Tape & Reel	04N070H

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	40	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _C = 25°C)	I _D	57	A
Continuous Drain Current (T _C = 100°C)		40	
Continuous Drain Current (T _A = 25°C) *1		14.5	
Continuous Drain Current (T _A = 100°C) *1		10	
Pulsed Drain Current (t _p = 10μs, T _C = 25°C)	I _{DM}	228	A
Single Pulse Avalanche Energy *3	E _{AS}	45	mJ
Power Dissipation (T _C = 25°C)	P _D	43	W
Power Dissipation (T _A = 25°C) *1		2.7	
Operating Junction Temperature Range	T _J	-55 ~ +175	°C
Storage Temperature Range	T _{STG}	-55 ~ +175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	-	3.5	°C/W
Thermal Resistance Junction-to-Air *1	R _{θJA}	-	-	55	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 32V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V,I _D = 15A	-	6.7	7.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	2.8	4	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	5.5	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	1040	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 20V	-	460	-	
C _{RSS}	Reverse Transfer Capacitance	f = 100kHz	-	10	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *4	V _{DD} = 20V	-	6	-	ns
t _r	Turn-on Rise Time *4	V _{GS} = 10V	-	40	-	
t _{d(OFF)}	Turn-Off Delay Time *4	I _D = 20A	-	22	-	
t _f	Turn-Off Fall Time *4	R _G = 5Ω	-	11	-	
Q _G	Total Gate-Charge	V _{DD} = 20V	-	14.7	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 10V	-	3.9	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 15A	-	3.1	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _S = 15A, V _{GS} = 0V	-	0.86	1.2	V
trr	Reverse Recovery Time	I _S = 15A, V _{GS} = 0V	-	60	-	ns
Qrr	Reverse Recovery Charge	di/dt = 100A/μs	-	53	-	nC

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 20V, V_{GS} = 10V, L = 0.5mH$
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

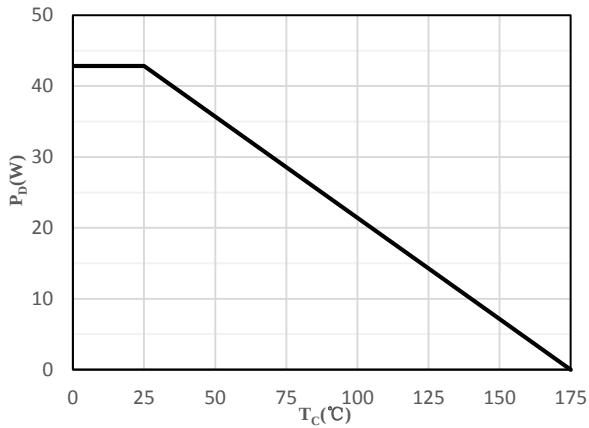


Fig 1 Power Dissipation

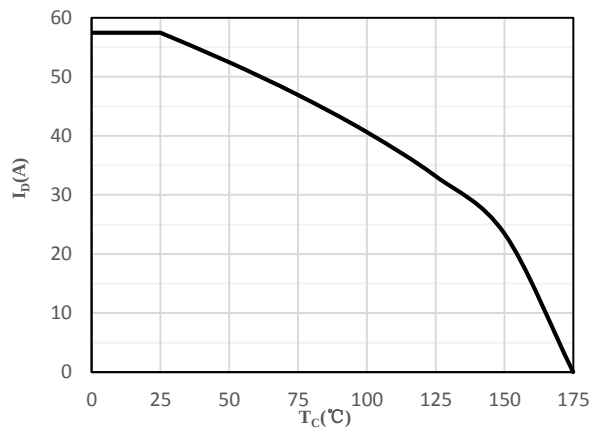


Fig 2 Drain Current

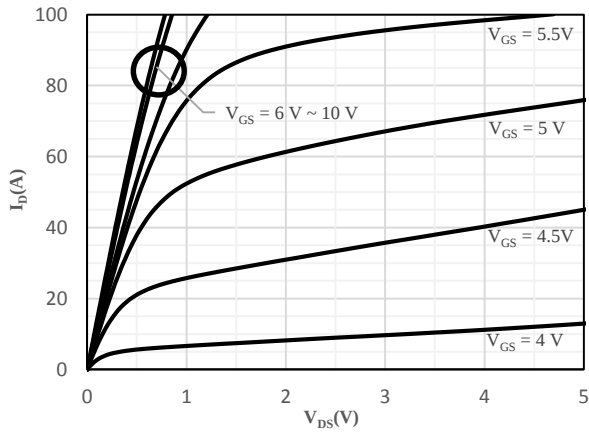


Fig 3 Typical Output Characteristics

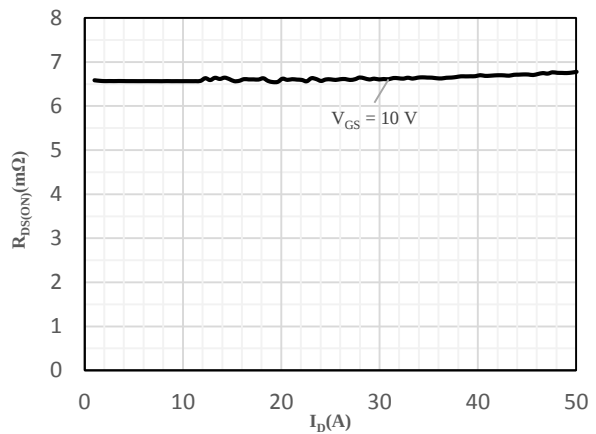


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

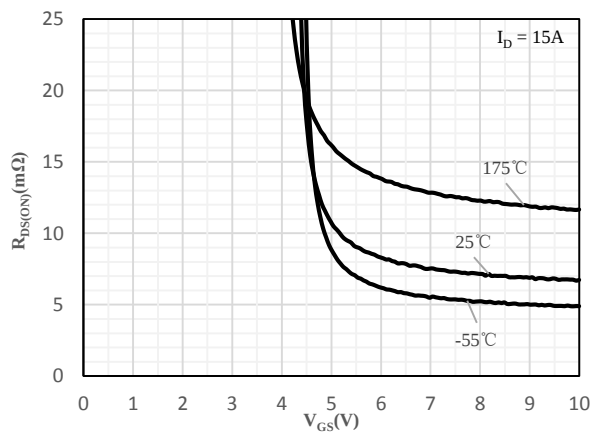


Fig 5 On-Resistance vs. Gate-Source Voltage

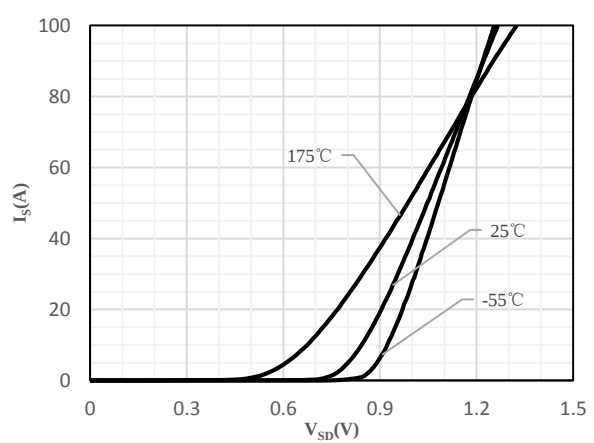


Fig 6 Body-Diode Characteristics

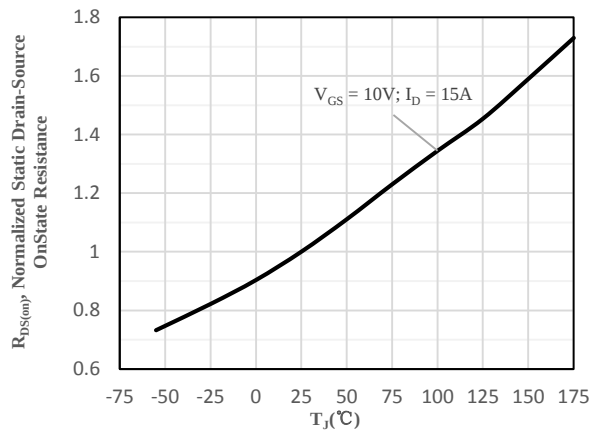


Fig 7 Normalized On-Resistance vs. Junction Temperature

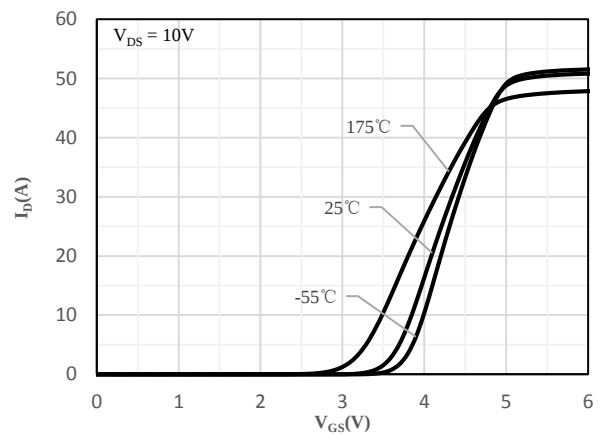


Fig 8 Transfer Characteristics

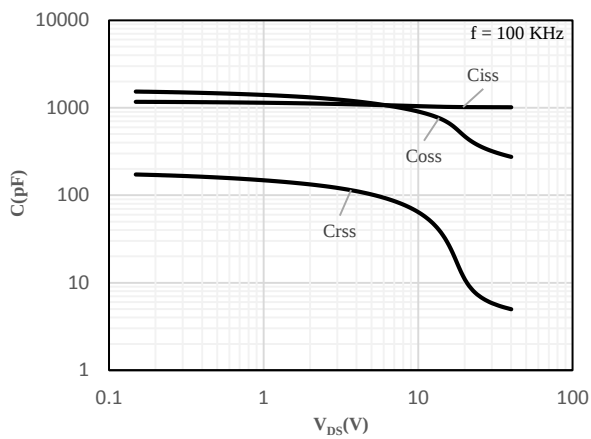


Fig 9 Capacitance Characteristics

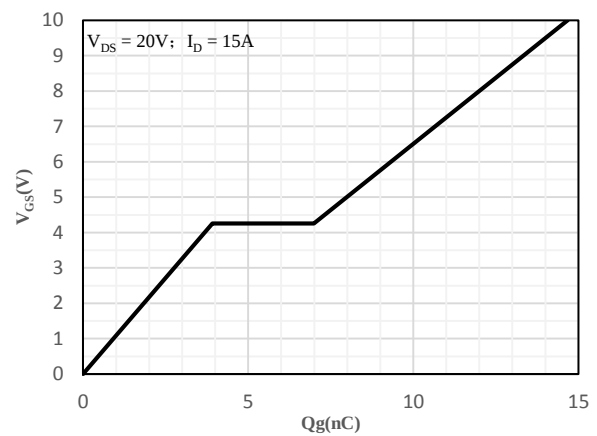


Fig 10 Gate-Charge Characteristics

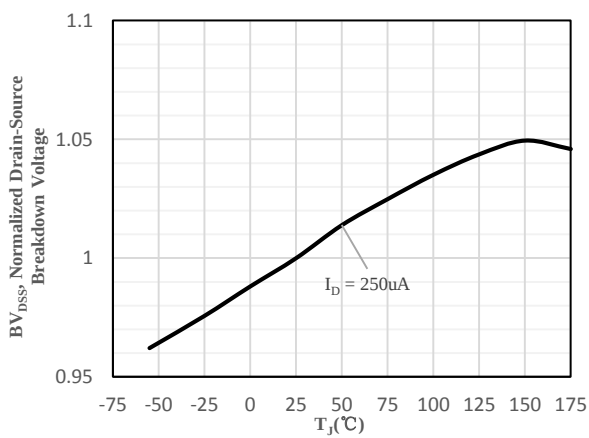


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

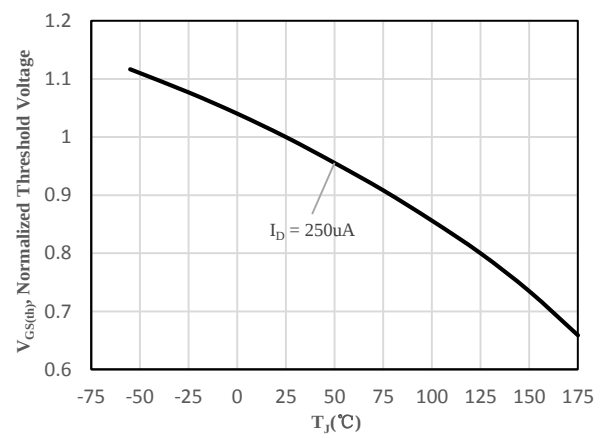
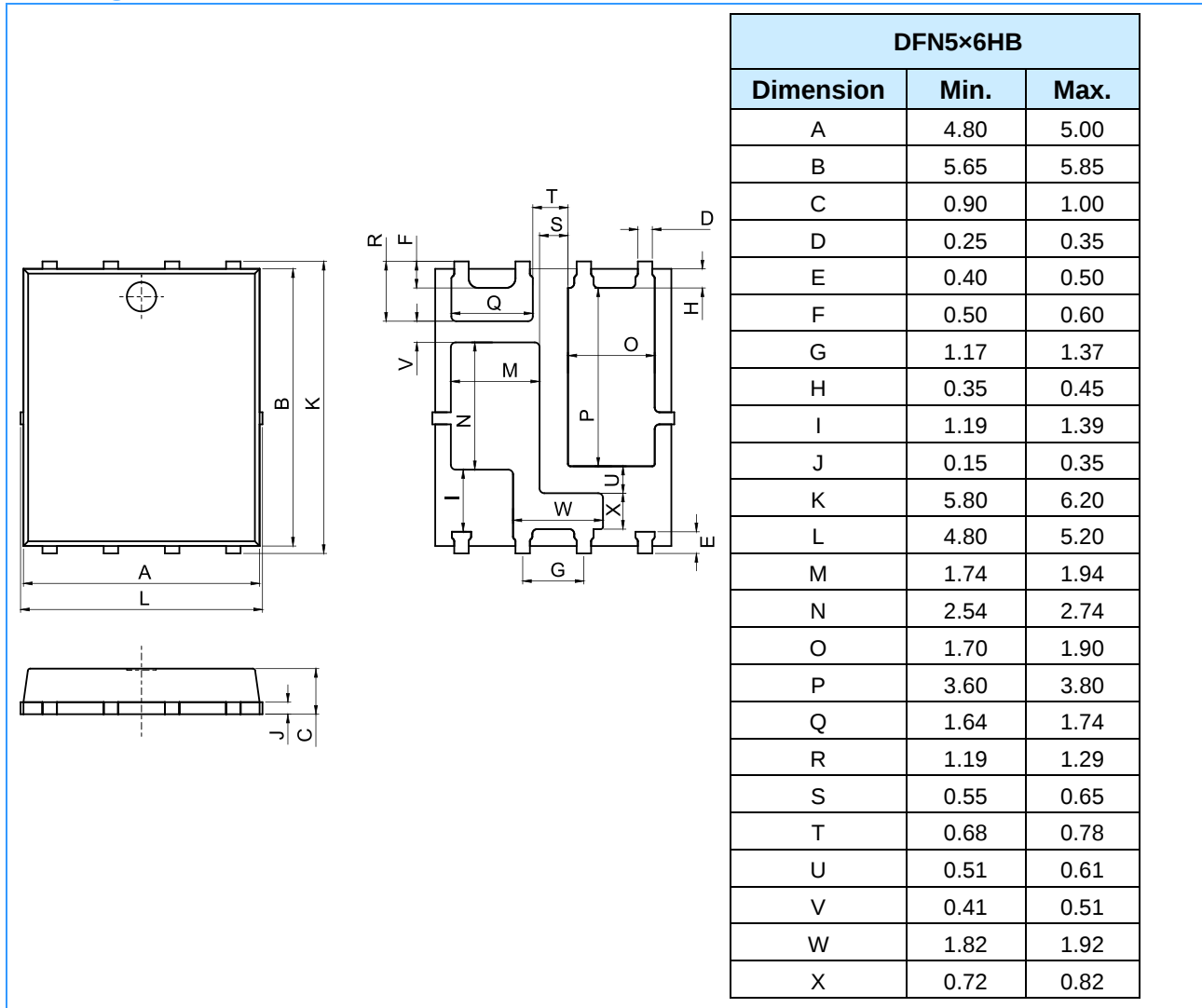


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)

